Data sheet acquired from Harris Semiconductor
SCHS136E

August 1997 - Revised October 2003

CD54HC85, CD74HC85, CD54HCT85, CD74HCT85

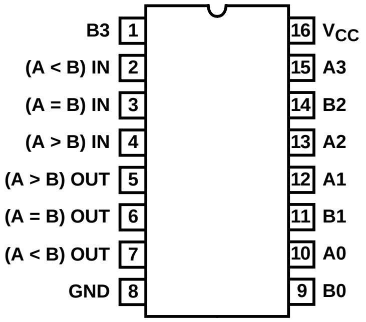
High-Speed CMOS Logic 4-Bit Magnitude Comparator

Features

- **Buffered Inputs and Outputs**
- **Typical Propagation Delay: 13ns (Data to Output at V_{CC} = 5V, C_L = 15pF, T_A = 25^{o}C**
- **Serial or Parallel Expansion Without External Gating**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^{o}C to 125^{o}C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30%of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Pinout

CD54HC85, CD54HCT85 (CERDIP)
CD74HC85 (PDIP, SOIC, SOP, TSSOP)
CD74HCT85 (PDIP, SOIC)
TOP VIEW



Description

The ’HC85 and ’HCT85 are high speed magnitude comparators that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

These 4-bit devices compare two binary, BCD, or other monotonic codes and present the three possible magnitude results at the outputs (A > B, A < B, and A = B). The 4-bit input words are weighted (A0 to A3 and B0 to B3), where A3 and B_3 are the most significant bits.

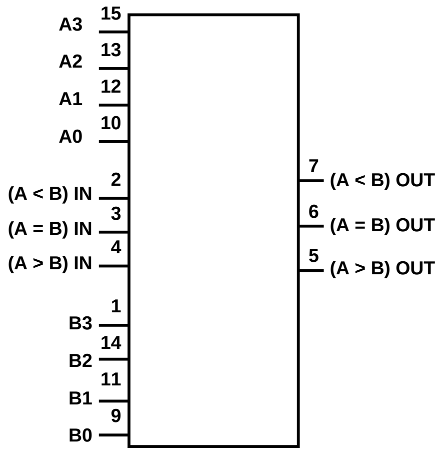
The devices are expandable without external gating, in both serial and parallel fashion. The upper part of the truth table indicates operation using a single device or devices in a serially expanded application. The parallel expansion scheme is described by the last three entries in the truth table.

Ordering Information

PART NUMBER	TEMP. RANGE (^{o}C)	PACKAGE
CD54HC85F3A	-55 to 125	16 Ld CERDIP
CD54HCT85F3A	-55 to 125	16 Ld CERDIP
CD74HC85E	-55 to 125	16 Ld PDIP
CD74HC85M	-55 to 125	16 Ld SOIC
CD74HC85MT	-55 to 125	16 Ld SOIC
CD74HC85M96	-55 to 125	16 Ld SOIC
CD74HC85NSR	-55 to 125	16 Ld SOP
CD74HC85PW	-55 to 125	16 Ld TSSOP
CD74HC85PWR	-55 to 125	16 Ld TSSOP
CD74HC85PWT	-55 to 125	16 Ld TSSOP
CD74HCT85E	-55 to 125	16 Ld PDIP
CD74HCT85M	-55 to 125	16 Ld SOIC
CD74HCT85MT	-55 to 125	16 Ld SOIC
CD74HCT85M96	-55 to 125	16 Ld SOIC

NOTE: When ordering, use the entire part number. The suffixes 96 and R denote tape and reel. The suffix T denotes a small-quantity reel of 250.

PFunctional Diagram



TRUTH TABLE

COMPARING INPUTS				CASCADING INPUTS			OUTPUTS		
A3, B3	**A2, B2**	**A1, B1**	**A0, B0**	**A > B**	**A < B**	**A = B**	**A > B**	**A < B**	**A = B**
SINGLE DEVICE OR SERIES CASCADING									
A3 > B3	X	X	X	X	X	X	H	L	L
A3 < B3	X	X	X	X	X	X	L	H	L
A3 = B3	A2 >B2	X	X	X	X	X	H	L	L
A3 = B3	A2 < B2	X	X	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 > B1	X	X	X	X	H	L	L
A3 = B3	A2 = B2	A1 < B1	X	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	X	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	L	L	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	H	L	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	H	L	L	H
PARALLEL CASCADING									
A3 = B3	A2 = B2	A1 = B1	A0 = B0	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	H	L	L	L	L
A3 = B3	A2 = B2S	A1 = B1	A0 = B0	L	L	L	H	H	L

H = High Voltage Level, L = Low Voltage, Level, X = Don’t Care

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
  For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ . . . . ±20mA
DC Output Diode Current, I_{OK}
  For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ . . . . ±20mA
DC Output Source or Sink Current per Output Pin, I_O
  For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} or I_{GND} . . . . ±50mA

Operating Conditions

Temperature Range (T_A) . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
  HC Types . . . . .2V to 6V
  HCT Types . . . . .4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . 0V to V_{CC}
Input Rise and Fall Time
  2V . . . . 1000ns (Max)
  4.5V. . . . . 500ns (Max)
  6V . . . . 400ns (Max)

Thermal Information

Package Thermal Impedance, θ_{JA} (see Note 1):
  E (PDIP) Package . . . . .67°C/W
  M (SOIC) Package. . . . . .73°C/W
  NS (SOP) Package . . . . 64°C/W
  PW (TSSOP) Package . . . . 108°C/W
Maximum Junction Temperature . . . . 150°C
Maximum Storage Temperature Range . . . .-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . 300°C
  (SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 2)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
A0-A3, B0-B3 and (A = B) IN	1.5
(A > B) IN, (A < B) IN	1

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g. 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, A_n, B_n to (A > B) OUT, (A < B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	195	-	245	-	295	ns
			4.5	-	-	39	-	47	-	59	ns
		C_L = 15pF	5	-	16	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	33	-	42	-	50	ns
A_n, B_n to (A = B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	175	-	240	-	265	ns
			4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	30	-	37	-	45	ns

Switching Specifications Input t_r, t_f = 6ns **(Continued)**

				25°C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**V_{CC} (V)**	**MIN**	**TYP**	**MAX**	**MIN**	**MAX**	**MIN**	**MAX**	**UNITS**
(A > B) IN, (A < B) IN, (A = B) IN to (A > B) OUT, (A < B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	140	-	175	-	210	ns
			4.5	-	-	28	-	35	-	42	ns
		C_L = 15pF	5	-	11	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	24	-	30	-	36	ns
(A > B) IN to (A = B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	120	-	150	-	180	ns
			4.5	-	-	24	-	30	-	36	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	20	-	26	-	31	ns
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	24	-	-	-	-	-	pF
Output Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF
HCT TYPES											
Propagation Delay, An, Bn to (A > B) OUT, (A < B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	37	-	46	-	56	ns
		C_L = 15pF	5	-	15	-	-	-	-	-	ns
An, Bn to (A = B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	40	-	50	-	60	ns
		C_L = 15pF	5	-	17	-	-	-	-	-	ns
(A > B) IN, (A < B) IN, (A = B) IN to (A > B) OUT, (A < B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
(A > B) IN to (A = B) OUT	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	-	31	-	39	-	47	ns
		C_L = 15pF	5	-	13	-	-	-	-	-	ns
Output Transition Times (Figure 1)	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	15	-	19	-	22	ns
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	26	-	-	-	-	-	pF
Input Capacitance	C_{IN}	-	-	-	-	10	-	10	-	10	pF

NOTES:

3. C_{PD} is used to determine the dynamic power consumption, per gate/package.
4. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

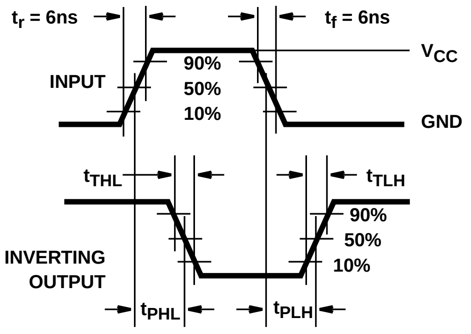


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

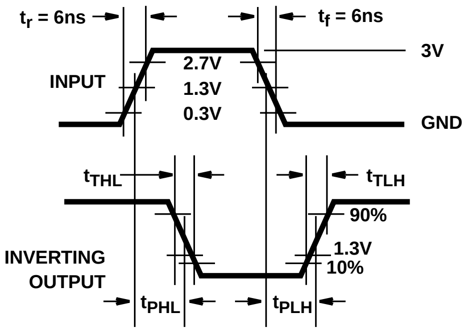


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

Test Circuits and Waveforms

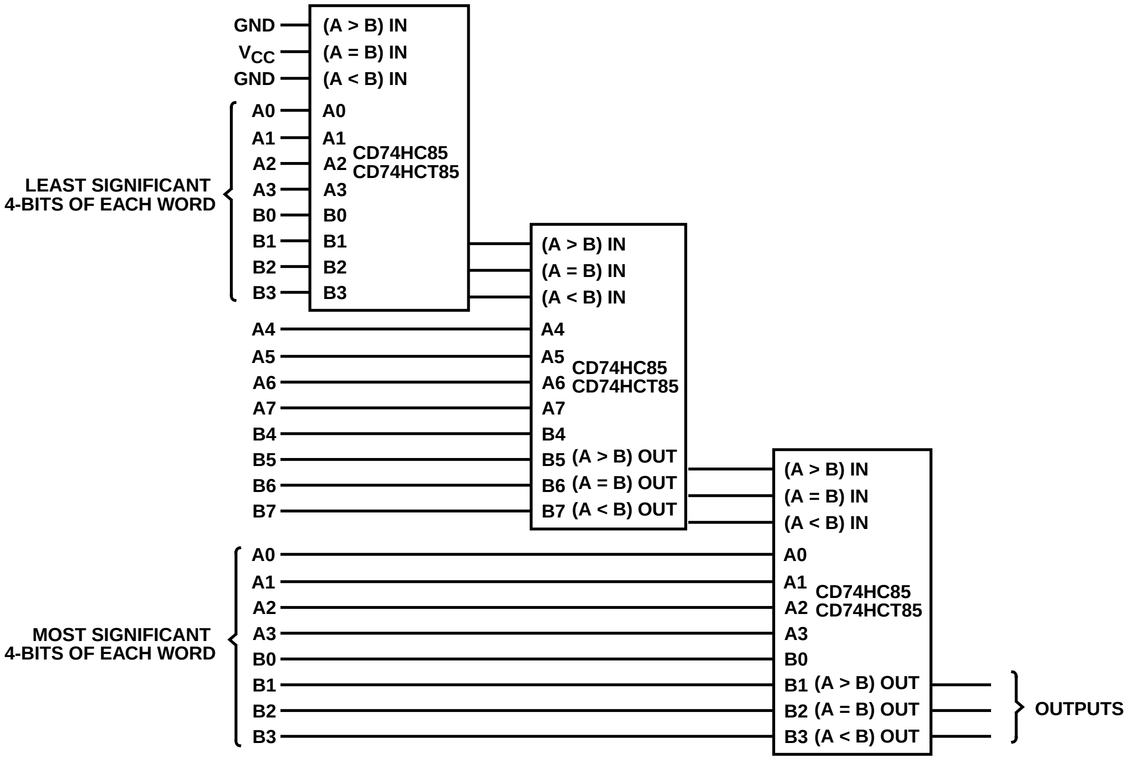


FIGURE 3. SERIES CASCADING - COMPARING 12-BIT WORDS

Test Circuits and Waveforms

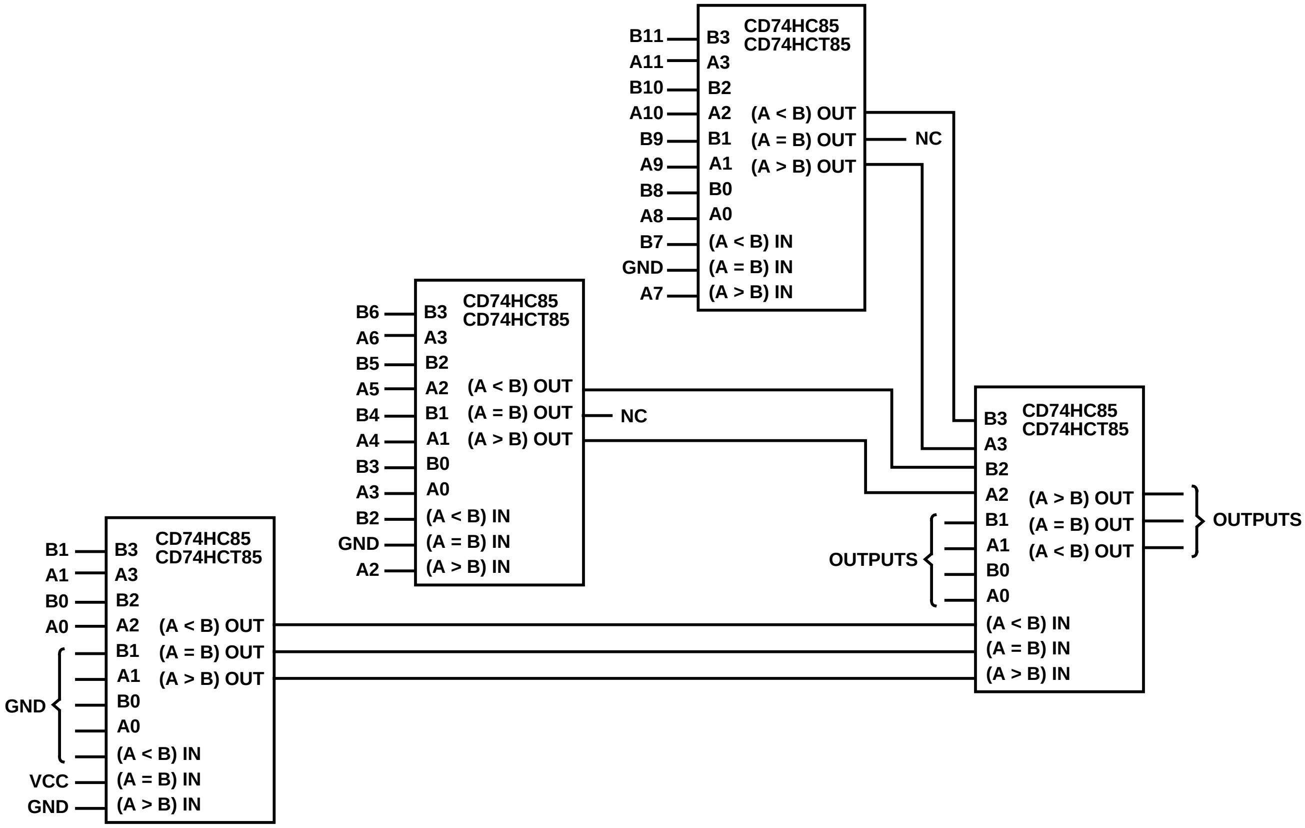


FIGURE 4. PARALLEL CASCADING - COMPARING 12-BIT WORDS